



# CERTIFICATE OF MAILING

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Joseph R. Jordan, Reg. No. 25,686

9/17/02  
Date

PATENT

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Serial No.: 10/O80,496  
Filed: February 22, 2002  
Applicant: Jozef Brcka  
Art Unit: 1741  
Title: MODIFIED TRANSFER FUNCTION DEPOSITION BAFFLES AND  
HIGH DENSITY PLASMA IGNITION THEREWITH IN  
SEMICONDUCTOR PROCESSING  
Attorney Docket: TAZ-213

Cincinnati, OH 45202

September 17, 2002

Assistant Commissioner for Patents  
Washington, D.C. 20231

## PRELIMINARY AMENDMENT

### In the Specification

Replace paragraph numbers [0004], [0006], [0007], [0012], [0014] and [0064],  
with the following amended paragraphs:

A' [0004] This invention relates to inductively-coupled plasma (ICP) sources used in the processing of semiconductors. The invention is particularly applicable to high-density inductively-coupled plasma (HDICP) sources in which RF energy is inductively coupled through a dielectric material that is protected by a slotted deposition baffle to energize a plasma for depositing an electrically conductive material onto, or etching an electrically conductive material from, a semiconductor wafer.

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01 FC:103  
02 FC:102

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